ABSTRACT

A semiconductor device includes an active fin extending in a first direction on an upper surface of a substrate and comprising a first fin portion and a second fin portion on the first fin portion; an isolation pattern between the first fin portion and the second fin portion; a gate structure intersecting the active fin and extending in a second direction intersecting the first direction; and source/drain regions in regions of the second fin portion on both sides of the gate structure, respectively. The gate structure includes a gate electrode intersecting a region of the active fin and extending in the second direction, a pair of gate spacers extending in the second direction along both side surfaces of the gate electrode in the first direction and including the same material as a material of the isolation pattern, and a gate insulating layer between the gate electrode and the active fin.

FIG. 4A